Low Capacitance Quad Array for ESD Protection

MSEMFxxLC

General Description

This integrated transient voltage suppressor • device (TVS) is designed for applications requiring transient overvoltage protection, printers, business • machines, communication systems, medical • equipment, and other applications. Its integrated • design provides very effective and reliable • protection for separate lines using only one • package. These devices are ideal for situations where board space is at a premium.

Applications

- Serial and Parallel Ports
- Microprocessor Based Equipment
- Notebooks, Desktops, Servers
- Cellular and Portable Equipment

Features

- Four Separate Unidirectional Configurations for Protection
- Low Leakage Current < 1 μ A @ 3Volts</p>
- Power Dissipation: 380mW
- Small SOT-553 SMT Package
- Low Capacitance
- Complies to USB 1.1 Low Speed & Speed Specifications
- Pb-Free package is available
 RoHS product for packing code suffix "G"
 Halogen free product for packing code suffix "H"

Complies with the following standards IEC61000-4-2

Level 4 15 kV (air discharge)

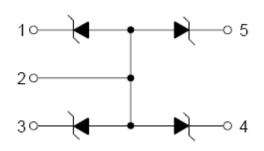
8 kV(contact discharge)

MIL STD 883E - Method 3015-7 Class 3 25 kV HBM (Human Body Model)

Functional diagram



SOT-553



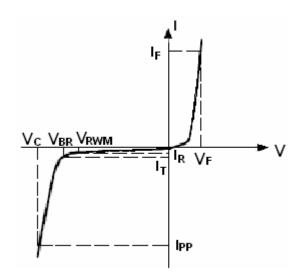
Maximum Ratings (T _A =25°C)							
Symbol	Parameter Value						
P _{PK}	Peak Power Dissipation($8 \times 20 \ \mu \ s@T_{A}=25 \ C$)	25	W				
PD	Steady State Power-1 Diode	380	mW				
R _{θ JA}	Thermal Resistance, Junction-to-Ambient	327	°C/W				
	Above 25°C, Derate	3.05	Mw/℃				
T _{Jmax}	Maximum Junction Temperature	150	°C				
$T_J T_{stg}$	Operation Junction and Storage Temperature Range	-55 to +150	°C				
TL	Lead Solder Temperature(10 seconds duration)	260	°C				



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Electrical Parameter

Symbol	Parameter				
I _{PP}	Maximum Reverse Peak Pulse Current				
Vc	Clamping Voltage @ I _{PP}				
V _{RWM}	Working Peak Reverse Voltage				
I _R	Maximum Reverse Leakage Current @ V _{RWM}				
Ι _Τ	Test Current				
V_{BR}	Breakdown Voltage @ I_T				
I _F	Forward Current				
V _F	Forward Voltage @ I _F				



Electrical Characteristics											
	V _{BR}						С				
Part Numbers	Min.	Тур.	Max.	Ι _Τ	V _{RWM}	I _R	Typ. 0v bias				
	V	V	V	mA	V	μA	pF				
MSEMF3V3LC	5.3	5.6	5.9	1	3.0	1.0	12				
MSEMF05LC	6.1	6.8	7.2	1	5.0	1.0	8				

1. Non-repetitive current per Figure 1.

2. Only 1 diode under power. For 4 diodes under power

3. Capacitance of one diode at f=1MHz, T_A =25 °C

Typical Characteristics

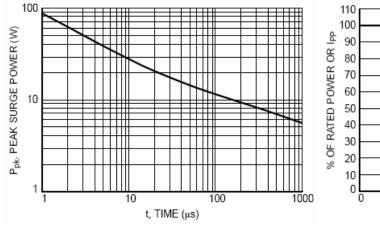


Figure 1 Pulse Width

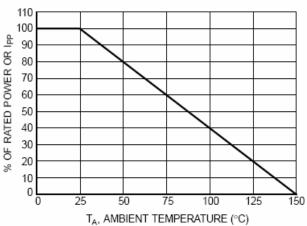
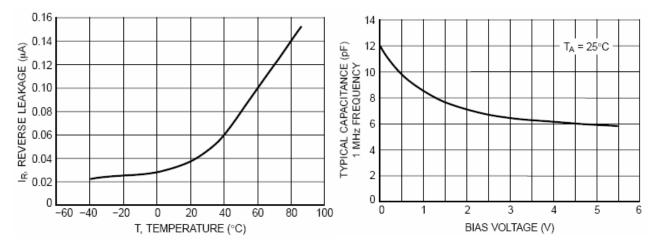


Figure 2 Power Derating Curve



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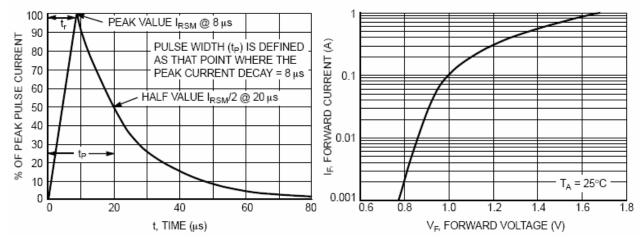
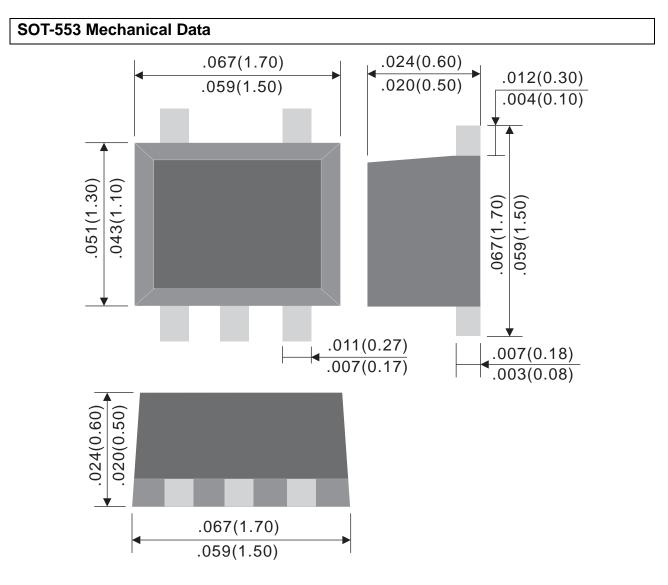


Figure 5 8*20 Pulse Waveform

Figure 6 Forward Voltage



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Dimensions in inches and (millimeters)

SOLDERING FOOTPRINT*

